

**Amendments to the Specification:**

Please replace the title at page 1, line 1, with the following amended title:

~~LASER IRRADIATION METHOD, LASER IRRADIATION APPARATUS AND~~  
~~METHOD FOR MANUFACTURING SEMICONDUCTOR DEVICE~~ METHOD OF  
FABRICATING SEMICONDUCTOR DEVICE UTILIZING LASER IRRADIATION

Please replace the paragraph bridging pages 25 and 26 with the following amended paragraph:

Next, a second etching treatment is carried out without removing the resist masks. Herein,  $\text{CF}_4$ ,  $\text{Cl}_2$ , and  $\text{O}_2$  are used for etching gas and the W film is etched selectively. At this time, second conductive layers 828b to 833b are formed by the second etching treatment. On the other hand, the first conductive layers 817a to 822a are hardly etched and second-shaped conductive layers 828 to 833 including first layers 828a to 833a and second layers 828b to 833b are formed.

Please replace the paragraph beginning at page 26, line 3, with the following amended paragraph:

Next as shown in Fig. 6B, a second doping treatment is carried out without removing the resist masks. In this case, a dose amount is reduced than that of the first doping treatment, and impurity element imparting n-type is introduced under a high acceleration voltage of 70 to 120 keV. This embodiment is carried out taking a dose amount as  $1.5 \times 10^{14} / \text{cm}^2$  and an acceleration voltage as 90 keV. The second doping treatment uses the second-shaped conductive layers 828 to 833 as masks and an impurity element is introduced also into the semiconductor layers in the lower part of the

second conductive layers 828b to 833b to form newly second high-concentration impurity regions 823a to ~~827a~~ and 827a, low-concentration impurity regions 823b to 827b, and channel regions 823c to 827c.

Please replace the paragraph beginning at page 26, line 13, with the following amended paragraph:

Next, after removing the resist masks, resist masks 834a and 834b are newly formed, and, a third etching treatment is carried out as shown in Fig. 6C. Etching treatment is carried out for about 30 seconds, using SF<sub>6</sub> and Cl<sub>2</sub> as etching gas in a gas flow of 50:10 and with RF (13.56 MHz) power of 500 W supplied to a coil-shaped electrode under pressure of 1.3 Pa to generate plasma. RF (13.56 MHz) power of 10 W is supplied to a substrate side (sample stage), whereby a substantially negative self-bias voltage is applied thereto. Accordingly, a p-channel type TFT and a TaN film of TFT (pixel TFT) in a pixel portion are etched by the third etching treatment to form third-shaped conductive layers 835 to 838 including first layers 835a to 838a and second layers 835b to 838b.